

27 - 960 MHz OOK/(G)FSK Transmitter SoC

MCU Features

- High-performance 8051
 - Single instruction cycle (1T-8051)
 - Up to 24 MIPS
 - 8 kB RAM / 8 kB OTP
 - Built-in 512 bits EEPROM
 - 12 kB ROM (API function library)
 - Single-wire online simulation debugging interface
- Digital peripherals
 - Built-in AES-128 acceleration engine
 - True random number generator
 - 1x UART
 - 1x SPI
 - 1x WDT
 - 1x RTC (internal 32 kHz and external 32.768KHz)
 - 2x 16-bit multifunction timer (supports PWM/CCP)
 - 16x GPIO, all supporting interrupt-on-change and wake-up
- Analog peripherals
 - Sub-1G transmitter module
 - 3D low-frequency wake-up module
 - 12-bit SAR-ADC, 100ksps, 12-ch
 - Built-in high speed 3 /12/ 24 MHz RC oscillator
 - Built-in low-power 32 kHz RC oscillator
 - Support for external 32.768 kHz crystal oscillator
- Code security
 - Built-in multi-level program protection achieving high security
 - Serial port (S3S interface) for programming with lock function

Low-power Features

- Operating temperature: - 40 °C ~ + 85 °C
- Operating voltage: 2.0 - 3.6 V
- Shutdown current: 300 nA
- RTC mode current: 800 nA
- Low-power wake-up: 4.6 uA @ 125 kHz

Sub-1G Transmitter Features

- Operating frequency range: 27 - 960 MHz
- Modulation mode: OOK, G/FSK
- Data rate
 - 0.5 – 40 kbps (OOK)
 - 0.5 – 200 kbps (G/FSK)
- Output power: +13 dBm (Max.)
- Operating current: 18mA @+13 dBm, 433.92 MHz FSK
- Dual transmission PAs
 - Single-ended and high-efficient Class E transmission PA
 - Differential transmission PA
- PA ramping slope varying according to rate

3D Low-frequency Wake-up Features

- Operating frequency: 20 - 200 kHz
- Data rate: 1 – 8 kbps
- Supporting 1/2/3 channels
- Supporting programmable 8/16/24/32-bit matching sync word
- Supporting programmable 8/16-bit matching ID
- Wake-up sensitivity of 70 uVrms
- Supporting low-power listening mode (DutyCycle)
- Supporting digital RSSI with a dynamic range of 80 dB

Packaging

- TSSOP28

Application

- Garage door remote control
- Remote access control system
- Consumer wireless remote control
- Smart home
- Home security
- Active RFID tags
- Wireless sensor network
- WM-Bus T1 mode

Description

Embedded with a 1T-8051 core, the CMT2163A is a low-power SoC RF transmitter enriched with below features.

1. The chip series supports wireless transmission @ 27 - 960 MHz with OOK or (G)FSK modulation.
2. High-efficient single-ended PA with an adjustable output power range of 0~+13dBm, consuming only a current of 18 mA for +13dBm transmission.
3. 8 kB OTP program bank and 12 kB ROM (for API library storage).
4. With 1-wire online simulation function, users can download the target debugging code directly to the on-chip PRAM through the dedicated 1-wire debugger, achieving more convenient debugging comparing with the troublesome debugging of traditional OTP chip with no online simulation supporting and a specific simulator required.
5. Supporting built-in AES-128 accelerator, true random number generator (TRNG), and 32-bit serial number (ID), fit for remote or active RFID applications requiring encrypted transmission.
6. Supporting dual-clock operating architecture, namely, the system operating with the internal high-speed clock meanwhile the internal low-power RC oscillation or external 32.768 kHz crystal oscillator operating for periodical wake-up from low-power mode.
7. Built-in 12-bit high-precision and high-speed SAR-ADC, fit for wireless sensor acquisition scenarios.



TSSOP28 9.70 x 6.40 x 1.2 mm

Ordering Information

Model	Package	MOQ
CMT2163A-ETR	TSSOP28 T&R	2500 pcs

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1 Electrical Specifications

If nothing else stated, all measurement results are obtained using the evaluation board CMT216xA-EM Rev001 under the conditions of $V_{DD} = 3.3\text{ V}$, $T_{OP} = 25^{\circ}\text{C}$, $F_{RF} = 433.92\text{ MHz}$, matching to $50\ \Omega$ impedance and +10 dBm output power.

1.1 Recommended Operating Conditions

Table 1. Recommended Operating Conditions

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Operating supply voltage	VDD	Temperature range is $-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$	2.0		3.6	V
Operating temperature	T_{OP}		- 40		+ 85	$^{\circ}\text{C}$
Supply voltage slope			1			mV/us

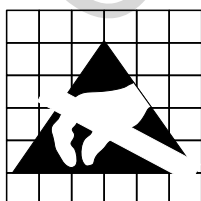
1.2 Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings^[1]

Parameter	Symbol	Condition	Min.	Typ.	Max.
Supply voltage	VDD		-0.3	3.6	V
Interface voltage	VIN		-0.3	$V_{DD} + 0.3$	V
Junction temperature	T_J		-40	125	$^{\circ}\text{C}$
Storage temperature	TSTG		-50	150	$^{\circ}\text{C}$
Soldering temperature	TSDR	Lasts for at least 30 seconds		255	$^{\circ}\text{C}$
ESD rating ^[2]		Human body model (HBM)	-2	2	kV
Latch-up current		@ 85°C	-100	100	mA

Notes:

- [1]. Exceeding *the Absolute Maximum Ratings* may cause permanent damage to the equipment. This value is a pressure rating and does not imply that the function of the equipment is affected under this pressure condition, but if it is exposed to absolute maximum ratings for extended periods of time, it may affect equipment reliability.
- [2]. The CMT216xA is a high performance RF integrated circuit. The operation and assembly of this chip should only be performed with good ESD protection.



Caution! ESD sensitive device. Precaution should be used when handling the device in order to prevent performance degradation or loss of functionality.

1.3 Transmitter Specifications

Table 3. Transmitter Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Frequency range	F _{RF}	HXOSC connecting 26 MHz crystal oscillator	27		480	MHz
			630		960	MHz
Data rate	DR	OOK	0.5		40	kbps
		(G)FSK	0.5		200	kbps
Output power range	P _{OUT}	Single-ended PA mode	0		+13	dBm
FSK frequency deviation range	F _{DEV}	630 ~ 960 MHz	1		300	kHz
		315 ~ 480 MHz	0.5		150	kHz
		210 ~ 320 MHz	0.33		100	kHz
		160 ~ 240 MHz	0.25		75	kHz
		105 ~ 160 MHz	0.17		50	kHz
Output power step	P _{STEP}			1		dB
Transmission startup time ^[1]	T _{PLL}	API tx_sym_prepare_for_transmission execution time		900		uS
FSK transmission current ^[2]	I _{DD-315F}	0dBm		7.9		mA
		+5dBm		10.0		mA
		+7dBm		11.4		mA
		+10dBm		14.0		mA
		+13dBm		17.0		mA
	I _{DD-434F}	0dBm		8.0		mA
		+5dBm		10.3		mA
		+7dBm		11.8		mA
		+10dBm		14.3		mA
		+13dBm		20.6		mA
	I _{DD-868F}	0dBm		9.2		mA
		+5dBm		12.2		mA
		+7dBm		13.8		mA
		+10dBm		17.7		mA
		+13dBm		23.5		mA
	I _{DD-915F}	0dBm		9.1		mA
		+5dBm		12.3		mA
		+7dBm		13.7		mA
		+10dBm		18.3		mA
		+13dBm		25.0		mA
OOK transmission current ^[3]	I _{DD-434O}	0dBm		6.5		mA
		+5dBm		7.2		mA
		+7dBm		7.8		mA
		+10dBm		8.5		mA
		+13dBm		12.0		mA

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
	I _{DD-868O}	0dBm		6.8		mA
		+5dBm		8.0		mA
		+7dBm		8.9		mA
		+10dBm		10.5		mA
		+13dBm		13.7		mA
Phase noise	PN ₄₃₄	100kHz frequency deviation		80		dBc/Hz
		200kHz frequency deviation		83		dBc/Hz
		400kHz frequency deviation		91		dBc/Hz
		600kHz frequency deviation		96		dBc/Hz
		1.2MHz frequency deviation		105		dBc/Hz
	PN ₈₆₈	100kHz frequency deviation		-77		dBc/Hz
		200kHz frequency deviation		-79		dBc/Hz
		400kHz frequency deviation		-87		dBc/Hz
		600kHz frequency deviation		-91		dBc/Hz
		1.2MHz frequency deviation		-100		dBc/Hz
Harmonic output	H2 ₃₁₅	2 nd harmonic @630MHz, +13dBm		< -45		dBm
	H3 ₃₁₅	3 rd harmonic @945MHz, +13dBm		< -45		dBm
	H2 ₄₃₄	2 nd harmonic @867.84MHz, +13dBm		< -45		dBm
	H3 ₄₃₄	3 rd harmonic @1301.76MHz, +13dBm		< -45		dBm
	H2 ₈₆₈	2 nd harmonic @1736MHz, +13dBm		< -36		dBm
	H3 ₈₆₈	3 rd harmonic @2604MHz, +13dBm		< -36		dBm
	H2 ₉₁₅	2 nd harmonic @1830MHz, +13dBm		< -36		dBm
	H3 ₉₁₅	3 rd harmonic @2745MHz, +13dBm		< -36		dBm
OOK adjusted extinction ratio			60		dB	
Occupied bandwidth	OBW ₃₁₅	A bandwidth of -20 dBc, RBW = 1kHz, SR = 1.2 kbps		6		kHz
	OBW ₄₃₄	A bandwidth of -20 dBc, RBW = 1kHz, SR = 1.2 kbps		7		kHz
Notes						
[1]. This item already includes the crystal startup time.						
[2]. It includes the 8051 core current. HFOSC uses the internal 24 MHz high-speed RC as the clock source.						

1.4 Oscillator Specifications

Table 4. Oscillator Specification

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Parameter
High-speed oscillating frequency	Crystal frequency ^[1]	F_{HXOSC}			26		MHz
	Frequency precision ^[2]				±20		ppm
	Load capacitor	$C_{HX-LOAD}$			15		pF
	Equivalent resistance	R_{HX-ESR}				60	Ω
	Startup time ^[3]	t_{HXOSC}			400		us
32.768 KHz crystal oscillator	Crystal frequency ^[1]	F_{LXOSC}			32.768		KHz
	Frequency precision ^[2]						ppm
	Load capacitor	$C_{LX-LOAD}$			9	12.5	pF
	Equivalent resistance	R_{LX-ESR}			50	90	KΩ
	Startup time ^[3]	t_{LXOSC}			1		s
Internal high speed RC oscillator	RC oscillating frequency	F_{HF-RC}		3	24	24	MHz
	Frequency precision ^[4]				1		%
Internal 32 kHz RC oscillator	Oscillator frequency	F_{LP-RC}			32		kHz
	Frequency precision ^[4]				1		%
Notes:							
[1]. An external reference clock can be used to drive the XTAL pin directly through a coupling capacitor. It's required the peak-to-peak level of the external reference clock is between 0.3 and 0.7 V.							
[2]. It involves:(1) initial tolerance, (2) crystal loading, (3) aging, and (4) temperature changing. The acceptable crystal frequency tolerance is subject to the bandwidth of the receiver and the RF error between the receiver and its paired transmitter.							
[3]. This parameter is crystal dependent to a large degree.							
[4]. Frequency precision is the value after calibration, which is related to environmental factors. Users can initiate calibration through calling the calibration API.							

1.5 EEPROM Specifications

Table 5. EEPROM Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Re- writing time	t_{EE-WR}	Call eeprom_write_words for ^[1]		14		ms/unit
		Call eeprom_set_dec_count ^[2]		42		ms
Number of programming times		Call eeprom_write_words ^[1]	10,000	100,000		cycles
		Call eeprom_set_dec_count ^[2]		1,000,000		cycles
Notes:						
[1]. The internal EEPROM is re-written by calling API eeprom_write_words for direct re-writing, and the operation address points to a 2-byte storage unit, namely, each unit is 2 bytes.						
[2]. The internal EEPROM is re-written by calling API eeprom_set_dec_count for enhanced re-writing. By applying Balanced Gray Code algorithm, it can endure more than 1,000,000 writing operations. It should be noted that the function is fixed to operating 3 units, namely, this field occupies 6 bytes with only the lower 22 bits data valid in the written value and the read value.						

1.6 3D Low-frequency Wake-up Performance

Table 6. 3D-LF RX Specification

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Low-frequency range	LF_{Range}	Operating frequency range	15	125	200	kHz
Operating current	$I_{single_carrier_RC}$	Power consumption when single channel in operating (using internal RC clock for carrier detection)		4.6		uA
	$I_{scan_carrier_RC}$	Power consumption when multiple channels in operating		4.6		uA
	$I_{single_snr_RC}$	Power consumption when single channel in operating (SNR detection)		5.7		uA
	$I_{scan_snr_RC}$	Power consumption when multiple channels in operating		5.7		uA
	$I_{single_carrier_EXT}$	Power consumption when single channel in operating (using an external 32.768 kHz crystal clock for carrier detection)		4.8		uA
	$I_{scan_carrier_EXT}$	Power consumption when multiple channels in operating		4.8		uA
	$I_{single_snr_EXT}$	Power consumption when single channel in operating		5.9		uA
	$I_{scan_snr_EXT}$	Power consumption when multiple channels in operating		5.9		uA

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
	I_{RC_DECODE}	Power consumption when decoding (data output is not connected to load)		5.7		μA	
	$I_{150/300_Fix_DC_RC}$	Fixed duty cycle mode, RX_time = 150 ms, Sleep_time = 300 ms		2.8		μA	
	$I_{150/600_Fix_DC_RC}$	Fixed duty cycle mode, RX_time = 150 ms, Sleep_time = 600 ms		2.4		μA	
	$I_{5/10_Extend_RC}$	Auto-extended duty cycle mode, Rx_time = 5 ms, Sleep_time = 10 ms		2.9		μA	
	$I_{5/20_Extend_RC}$	Auto-extended duty cycle mode, Rx_time = 5 ms, Sleep_time = 20ms		2.5		μA	
	$I_{5/40_Extend_RC}$	Auto-extended duty cycle mode, Rx_time = 5 ms, Sleep_time = 40 ms		2.2		μA	
	$I_{5/80_Extend_RC}$	Auto-extended duty cycle mode, Rx_time = 5 ms, Sleep_time = 80 ms		2.0		μA	
Sensitivity	$S_{Carrier_Detect}$	Data rate of 1 kbps		65		μV_{rms}	
		Data rate of 2 kbps		65		μV_{rms}	
		Data rate of 4 kbps		70		μV_{rms}	
		Data rate of 8 kbps		80		μV_{rms}	
	S_{SNR_Detect} SNR=8dB	Data rate of 1 kbps			70		μV_{rms}
		Data rate of 2 kbps			70		μV_{rms}
		Data rate of 4 kbps			70		μV_{rms}
		Data rate of 8 kbps			70		μV_{rms}
Startup time ^[2]	T_{LF_STR}	3D-LF RX startup settling time		1		ms	
Notes:							
[1]. The startup time means the stabilization time dedicated for starting the 3D-LF module after the software initialization is completed.							

1.7 High-precision ADC Performance

Table 7. High-precision ADC Specification

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Resolution	R_{ADC}			12		bit
Effective number of bits	NOEB			10		bit
Conversion input range	V_{AIN}		0		V_{REF}	V
ADC clock frequency	f_{ADC}		0.5	1.0	2.0	MHz
ADC total conversion time	t_{CONV}		16	16	25	
Sampling time ^[1]	t_{SAMP}		2	2	8	$1/F_{ADC}$

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Successive approximation conversion time ^[2]	t_{SAR}		13	13	16	
Data update time	t_{UPDATE}		1	1	1	
ADC data refresh rate	f_S	$F_{ADC} = 1 \text{ MHz}$		62.5		kHz
Stabilization time ^[3]	t_{STAB}				10	μS
Offset error	E_{OS}	$F_{ADC} = 1 \text{ MHz}$		± 4		LSB
Gain error	E_G	$F_{ADC} = 1 \text{ MHz}$		± 4		LSB
Integral nonlinearity error	INL	$F_{ADC} = 1 \text{ MHz}$		± 5		LSB
Differential nonlinearity error	DNL	$F_{ADC} = 1 \text{ MHz}$		± 4		LSB
ADC reference voltage Regulator output Bandgap reference External input reference ^[4]	V_{REF}	Input from B6 pin	1.0	V_{DDA} 1.2	V_{DDA}	V
Supply voltage range	V_{BAT}		2.0		3.6	V
Operating voltage range	V_{DDA}		2.0	2.2	3.6	V
Operating current	I_{ADC}	$V_{DDA} = 2.2 \text{ V}$		220		μA
Power efficiency	P_E			7.6		pJ/Conv
Leakage current	$I_{LEAKAGE}$			2.2		nA
Notes: [1]. The sampling time can be configured by software. See <i>AN281 CMT216xA ADC and AFE User Guide</i> or <i>CMT216xA User Guide</i> for details. [2]. The successive approximation conversion time can be configured by software. See <i>AN281 CMT216xA ADC and AFE User Guide</i> or <i>CMT216xA User Guide</i> for details. [3]. The stabilization time refers to the analog circuit stabilization time after power-on, which depends on the system design. [4]. The external input reference voltage must be at least 1.0 V, otherwise the circuit may not work properly.						

1.8 Temperature Sensor Specifications

Table 8. Temperature Sensor Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Temperature measurement error ^[1]	T_{ERR}	VDD: 2.2 ~ 3.6 V TOP: -20 ~ +70 °C		TBD		°C
		VDD: 2.2 ~ 3.6 V TOP: -40 ~ +125 °C		TBD		
Temperature sensor circuit establishing time	t_{STAB}				5	us
Notes: [1]. Based on the average of two measurements.						

1.9 Supply Voltage Detection Specifications

Table 9. Supply Voltage Detection Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Battery measuring error ^[1]	V_{ERR}		-50		+50	mV
Battery sensor circuit establishing time	t_{STAB}				5	us
Notes: [1]. Based on the average of two measurements.						

1.10 Constant Current Source Drive Specifications

Table 10. Constant Current Source Drive Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
D2 port constant current driver current ^[1]	I_{D2_DRV}		0		+250	mA
D2 port current output error range	I_{D2_ERR}	Full output range		+10		%
Constant current source driver establishing time	t_{DRV_STAB}			5		us
Notes: [1]. The constant current source output current of D2 is adjustable. See AN281 CMT216xA ADC and AFE User Guide for details.						

1.11 DC Specifications

Table 11. DC Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Active mode operating current ^[1] (HFOSC selects internal 24 MHz high-speed RC oscillator)	I _{AM_24}	CLK_SYS_DIV=1, F _{SYSCLK} =24 MHz		2.15		mA
		CLK_SYS_DIV=2, F _{SYSCLK} =12 MHz		1.56		mA
		CLK_SYS_DIV=4, F _{SYSCLK} =6 MHz		1.25		mA
		CLK_SYS_DIV=8, F _{SYSCLK} =3 MHz		1.09		mA
		CLK_SYS_DIV=16, F _{SYSCLK} =1.5 MHz		1.00		mA
Active mode operating current (HFOSC selects internal 12 MHz high-speed RC oscillator)	I _{AM_12}	CLK_SYS_DIV=1, F _{SYSCLK} =12 MHz		1.22		mA
		CLK_SYS_DIV=2, F _{SYSCLK} =6 MHz		0.91		mA
		CLK_SYS_DIV=4, F _{SYSCLK} =3 MHz		0.75		mA
		CLK_SYS_DIV=8, F _{SYSCLK} =1.5 MHz		0.67		mA
Active mode operating current (HFOSC selects internal 3 MHz high-speed RC oscillator)	I _{AM_3}	CLK_SYS_DIV=1, F _{SYSCLK} =3 MHz		0.49		mA
		CLK_SYS_DIV=2, F _{SYSCLK} =1.5 MHz		0.41		mA
Sleep mode (deep sleep)	I _{SDN}	Call sys_shutdown function, then LFOSC module is disabled		300		nA
Sleep mode (RTC)	I _{RTC}	Call sys_shutdown function, then the internal LFOSC module is enabled and the internal LPOSC (32 kHz) is selected.		800		nA
OTP code loading ^[2]	I _{LOAD}			4.6		mA

Notes: [1]. The program runs the While(1) loop, and the GPIO has no load.

1.12 AC Specifications

Table 12. AC Specifications

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
High level output	V _{OH}	Load is 1 k Ω , VDD = 3.3 V	VDD-0.4			V
Low level output	V _{OL}	Load is 1k Ω , VDD = 3.3 V			0.4	V
High level input	V _{IH}	VDD = 3.3 V		0.7*VDD		V
		VDD = 2.0 V		0.7*VDD		V
Low level input	V _{IL}	VDD = 3.3 V		0.2*VDD		V
		VDD = 2.0 V		0.2*VDD		V
Port leakage current	I _{LKG}	VDD = 2.0 V – 3.6 V		TBD		nA

1.13 Typical Performance of High-frequency Transmission

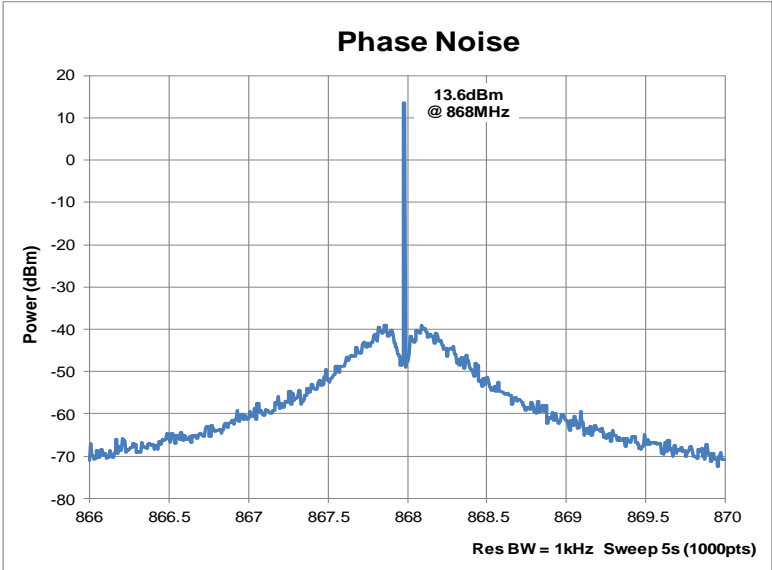


Figure 1. Phase Noise @ $F_{RF} = 868 \text{ MHz}$, $P_{OUT} = +13 \text{ dBm}$, un-modulated

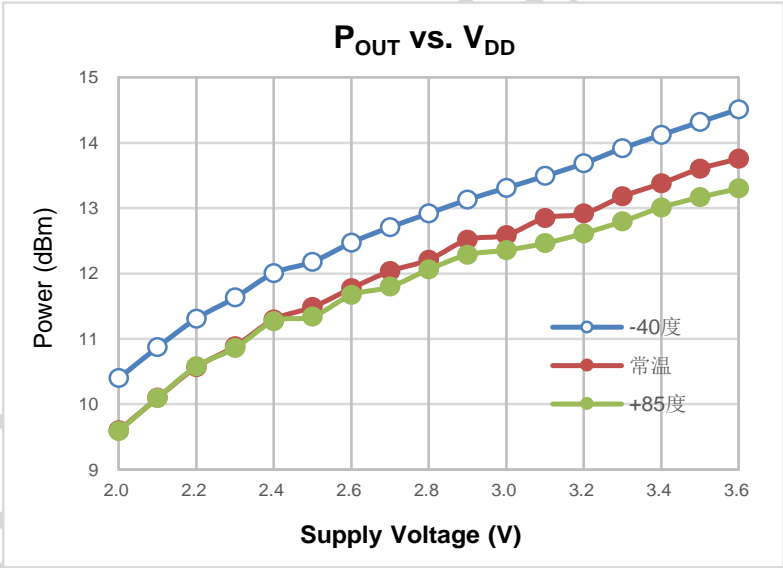


Figure 2. Output Power Vs. Supply Voltage

$F_{RF} = 433.92 \text{ MHz}$, $P_{OUT} = +13 \text{ dBm}$

2 Pin Description

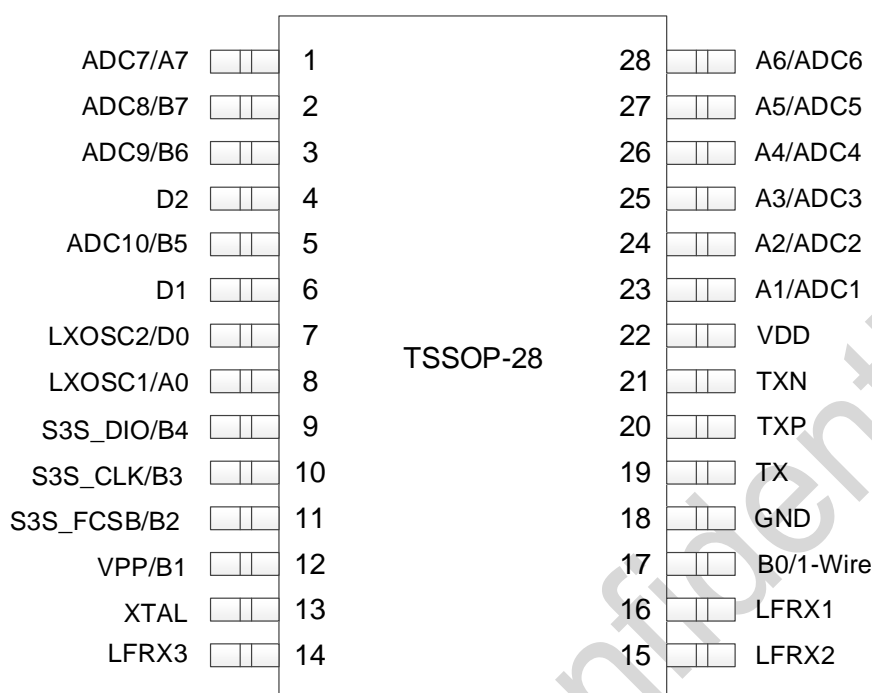


Figure 3. CMT2163A TSSOP28 Pin Arrangement

Table 13. CMT2163A Pin Description

Pin#	Name	Type	Description
1	A7/ADC7	IO	A7
		A	ADC7
2	B7/ADC8	IO	B7
		A	ADC8
3	B6/ADC9	IO	B6
		A	ADC9
4	D2	IO	Constant current source output driver port
5	B5/ADC10	IO	B5
		A	ADC10
6	D1	IO	GPIO16, one of the general purpose GPIOs
7	LXOSC2/D0	--	D0
		A	LXOSC2
8	LXOSC1/A0	IO	A0
		A	LXOSC1
9	S3S_DIO/B4	IO	B4
		IO	S3S_DIO
10	S3S_CLK/B3	IO	B3
		IO	S3S_CLK
11	S3S_FCSB/B2	IO	B2

Pin#	Name	Type		Description
		IO	S3S_FCSB	Chip programming bus S3S, namely programming chip selection line
12	VPP/B1	IO	B1	GPIO9, one of the general purpose GPIOs
		A	VPP	Chip OTP programming VPP, namely 6.5 V voltage input pin
13	XTAL	A		Crystal input pin, connecting to 26 MHz crystal to GND. See <i>Section 1.4 Oscillator</i> specifications for details.
14	LFRX3	A		Low-frequency wake-up Z-axis antenna input pin
15	LFRX2	A		Low-frequency wake up Y-axis antenna input pin
16	LFRX1	A		Low-frequency wake up X-axis antenna input pin
17	1-Wire/B0	IO	B0	GPIO8, one of the general purpose GPIOs
		IO	1-Wire	1-wire debugging line
18	GND	A		Power supply- input pin
19	TX	A		High-frequency transmission single-ended PA output pin
20	TXP	A		High-frequency transmission differential PA+ output pin
21	TXN	A		High-frequency transmission differential PA- output pin
22	VDD	A		Power+ input pin
23	A1/ADC1	IO	A1	GPIO1, one of the general purpose GPIOs
		A	ADC1	ADC1, ADC sampling channel 1
24	A2/ADC2	IO	A2	GPIO2, one of the general purpose GPIOs
		A	ADC2	ADC2, ADC sampling channel 2
25	A3/ADC3	IO	A3	GPIO3, one of the general purpose GPIOs
		A	ADC3	ADC3, ADC sampling channel 3
26	A4/ADC4	IO	A4	GPIO4, one of the general purpose GPIOs
		A	ADC4	ADC4, ADC sampling channel 4
27	A5/ADC5	IO	A5	GPIO5, one of the general purpose GPIOs
		A	ADC5	ADC5, ADC sampling channel 5
28	A6/ADC6	IO	A6	GPIO6, one of the general purpose GPIOs
		A	ADC6	ADC6, ADC sampling channel 6

3 Functional Description

Embedded with a Sub-1 GHz OOK / (G)FSK transmitter, the CMT2163A is a high-performance 8051 SoC, suitable for low-power wireless transmission applications in the 27 - 960 MHz band. The series chips integrate the below major modules ^[1].

- High-performance 8051 core with rich peripheral resources.
- Sub-1G OOK / (G) FSK transmission module.
- 3D low-frequency receiving/wake-up module (LFRX).
- Multi-channel 12-bit high-precision successive approximation ADC.

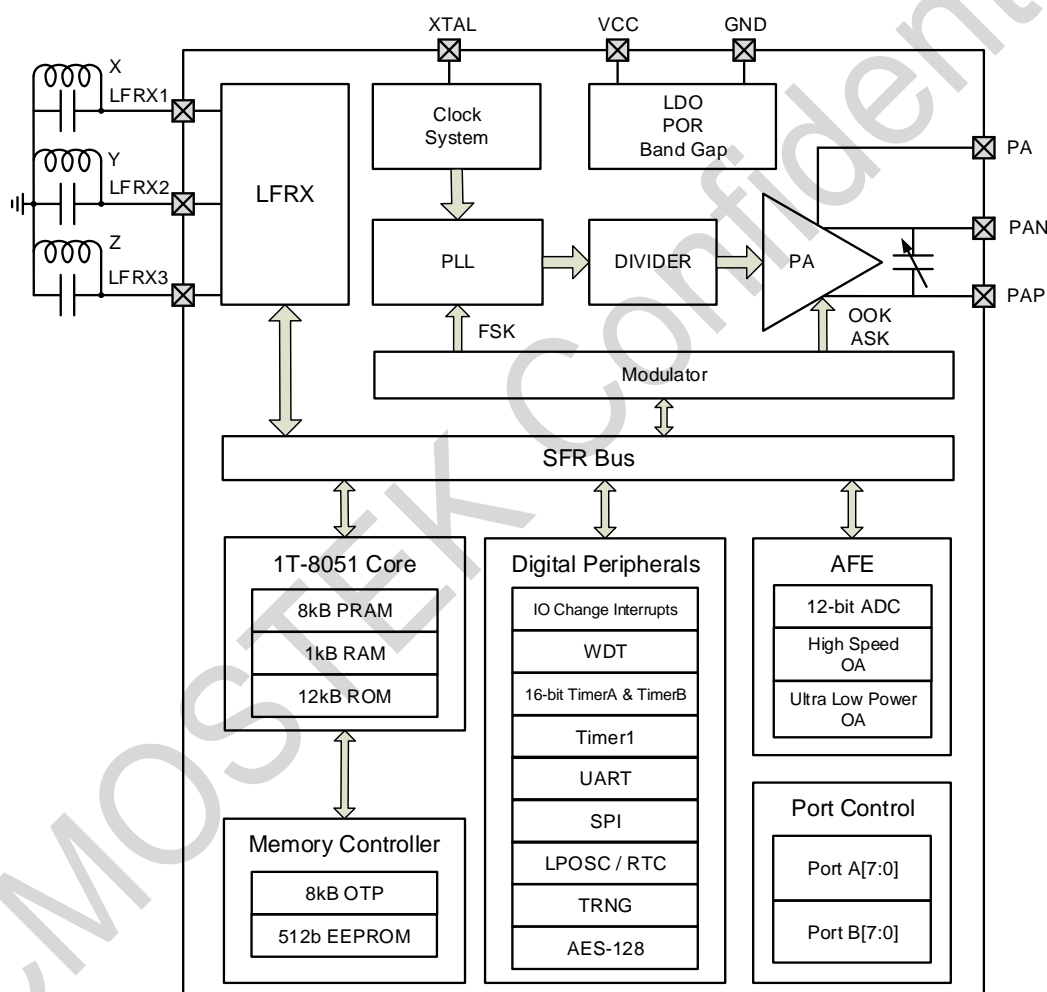


Figure 4. System Block Diagram

Notes:

1. This is the general block diagram for CMT216xA series. Different product models consist of different module combinations, namely not all models provide the full function modules.

3.1 High-performance 8051

Built-in with enhanced 1T-8051 and 24 MHz high-speed RC oscillator, the CMT2163A supports dual-clock operating mode, achieving 24 MIPS high-speed operating. Meanwhile, the low-speed clock is provided by the internal low-speed 32 kHz RC oscillator or external 32.768 kHz crystal oscillator, serving as the clock source of the low-power RTC.

For memory architecture, the on-chip 8 kB OTP ROM is for code storage, 8 kB PRAM for code running, 1 kB XRAM for data storage and 512 bits EEPROM for key data storage in case of power loss. Meanwhile, it integrates 12 kB MASK ROM for the storage of API library function of various chip modules.

For digital peripherals, it supports on-chip AES-128 operation acceleration engine, true random number generator, one UART, one SPI, watchdog, two 16-bit multi-function timers, one RTC, and 16 ports with multiplexing functions.

For development and debugging, the CMT216xA series chips adopt 1-wire debugging interface, which requires only one single wire connecting to the debugger to download code to PRAM, achieving simple and convenient online debugging.

3.2 Sub-1G Transmission Module

The CMT2163A integrates a high-performance Sub-1G transmitter which is embedded with dual transmission PA, that is,

- High-efficiency single-ended Class E PA, reaching a transmission power of +13 dBm while consuming only a current of 18 mA.
- Simple peripheral differential PA with built-in antenna auto-tuning function.

The transmitter supports 3 modulation modes, OOK, GFSK and FSK. Applying the fractional phase-locked loop technology, it requires only one 26 MHz crystal oscillator to achieve most of the 27~960 MHz band coverage.

3.3 3D Low-frequency Receiving/waking-up Module

Integrating a 3D low-frequency receiving/waking-up module, the CMT2163A supports operating in listening mode with a low power consumption of 4.6 μ A, reaching a wake-up sensitivity of 70 μ Vrms. It supports digital RSSI with a dynamic range of 80 dB. This product model is a suitable for various active RFID based near-field identification application scenarios.

3.4 12-bit High-precision ADC

Embedded with a multi-channel 12-bit high-precision successive approximation ADC along with a buffer based operational amplifier, it can fulfill high-resistance signal conditioning, fit for a variety of sensor acquisition applications.

4 Ordering Information

Table 14. CMT2163A Ordering Information

Model	Description	Packaging	Package Option	Operating Condition	Minimum Ordering Quantity
CMT2163A-ETR ^[1]	27 - 960 MHz transmitter SoC	TSSOP28	T&R	2.0 to 3.6 V, - 40 to 85 °C	2500

Notes:

[1]. E refers to extended Industrial product rating, which supports a temperature range from -40 to +85 °C.
T refers to the packaging type TSSOP28.
R refers to Tape & Reel package type, and the minimum ordering quantity (MOQ) is 2500 pieces.

Please visit www.cmostek.com for more product/product line information.

Please contact sales@cmotek.com or your local sales representative for sales or pricing requirements.

5 Packaging Information

The packaging information of the CMT2163A is shown in the below figure.

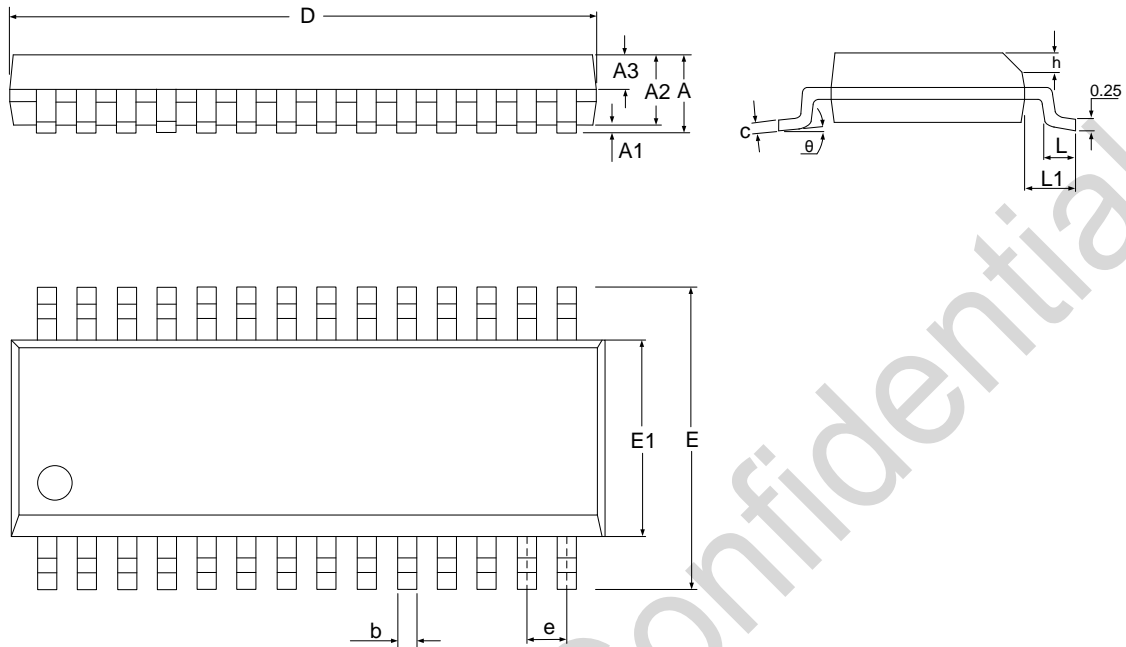


Figure 5. TSSOP28 Packaging

Table 15. TSSOP28 Packaging Scale

Symbol	Scale (mm)		
	Min.	Typ.	Min.
A	--	--	1.20
A1	0.05	--	0.15
A2	0.80	--	1.00
A3	0.39	0.44	0.49
b	0.20	--	0.29
c	0.14	--	0.18
D	9.60	9.70	9.80
E	6.20	6.40	6.60
E1	4.30	4.40	4.50
e	0.65 BSC		
L	0.45	0.60	0.75
L1	1.00 BSC		
θ	0	-	8°

6 Top Marking

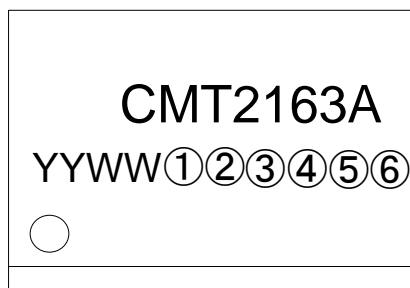


Figure 6. CMT2163A Top Marking

Table 16. CMT2163A Top Marking Information

Marking Method	Laser
Pin 1 Mark	Diameter of the circle = 1 mm
Font Size	0.6 mm, align right
Font Width	0.4 mm
Line 1 Marking	CMT2163A refers to model CMT2163A.
Line 2 Marking	YYWW is the date code assigned by the package factory. YY is the last 2 digit of the year. WW is the working week. ①②③④⑤⑥ is the internal tracing code.

7 Related Documents

Table 17. CMT2163A Related Documents

Doc No.	Document Name	Description
AN290	CMT216x User Guide	CMT216xA series chips user guide.
AN280	CMT216xA Low-frequency Receiving Function User Guide	CMT216xA 3D low-frequency receiving function user guide.
AN281	CMT216xA ADC and AFE User Guide	CMT216xA series chip ADC and analog front end user guide.
AN282	CMT216xA API Function Library User Guide	CMT216xA series chip API function library user guide.
AN284	CMT216xA Development Environment Establishment and Debugging	CMT216xA development environment establishment and debugging quick start guide.
AN286	CMT216xA Register Guide	CMT216xA series chip SFR register detail description.

8 Revise History

Table 18. Revise History Records

Version No.	Chapter	Description	Date
0.6	All	Initial version	2019-07-01
0.7	All		2019-11-01

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9 Contacts

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